

# BD897

Silicon PNP Transistors



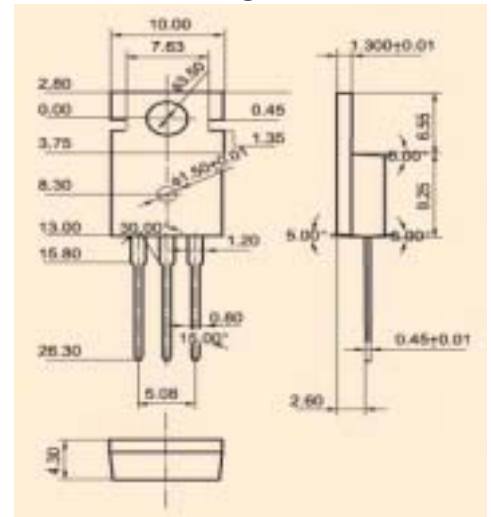
**B C E**

### ◆ Features

- . With TO-220 package
- . With general-purpose and amplifier applications

### ◆ Absolute Maximum Ratings Tc=25°C

SYMBOL	PARAMETER	RATING	UNIT
V <sub>CB0</sub>	Collector to base voltage	60	V
V <sub>CEO</sub>	Collector to emitter voltage	60	V
V <sub>EBO</sub>	Emitter to base voltage	5.0	V
I <sub>B</sub>	Base collector current		
I <sub>C</sub>	Collector current	8.0	A
P <sub>C</sub>	Collector power dissipation	70	W
T <sub>j</sub>	Junction temperature	150	°C
T <sub>stg</sub>	Storage temperature	-55~150	°C



TO-220

### ◆ Electrical Characteristics Tc=25°C

SYMBOL	PARAMETER	CONDITIONS	MIN	TYPE	MAX	UNIT
I <sub>CB0</sub>	Collector-base cut-off current	V <sub>CB</sub> =60V; I <sub>E</sub> =0			0.2	mA
I <sub>EBO</sub>	Emitter-base cut-off current	V <sub>EB</sub> =5.0V; I <sub>C</sub> =0			2.0	mA
I <sub>CEO</sub>	Collector-emitter cut-off current	V <sub>CE</sub> =60V; I <sub>B</sub> =0			0.5	mA
V <sub>CB0</sub>	Collector-base breakdown voltage					
V <sub>(BR)ceo</sub>	Collector-emitter breakdown voltage	I <sub>C</sub> =0.1A; I <sub>B</sub> =0	60			V
V <sub>EBO</sub>	Emitter-base breakdown voltage					
V <sub>CE(sat-1)</sub>	Collector-emitter saturation voltages	I <sub>C</sub> =3A; I <sub>B</sub> =12mA			2.5	V
V <sub>CE(sat-2)</sub>	Collector-emitter saturation voltages					
h <sub>FE-1</sub>	Forward current transfer ratio	I <sub>C</sub> =3A; V <sub>CE</sub> =3V	750			
h <sub>FE-2</sub>	Forward current transfer ratio					
h <sub>FE-3</sub>	Forward current transfer ratio					
V <sub>BE(on)1</sub>	Base-emitter on voltages	I <sub>C</sub> =3A; V <sub>CE</sub> =3V			2.5	V
V <sub>BE(on)2</sub>	Base-emitter on voltages					
f <sub>T</sub>	Transition frequency					
C <sub>ob</sub>	Output Capacitance					